	Application No.	Applicant(s)	-	
Notice of Allowability	10/050,639	LEE ET AL.	LEE ET AL.	
	Examiner	Art Unit		
	DuyVu n Deo	1765		
The MAILING DATE of this communication apperall claims being allowable, PROSECUTION ON THE MERITS IS therewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI	ears on the cover sheet with the co (OR REMAINS) CLOSED in this apport or other appropriate communication GHTS. This application is subject to and MPEP 1308.	will be mailed in due	course. THIS	
1. X This communication is responsive to the response filed 2/	<u>4/04</u>			
2. ☑ The allowed claim(s) is/are <u>60-88</u> .				
3. $igotimes$ The drawings filed on <u>15 January 2002</u> are accepted by the	e Examiner.			
4.				
 Attachment(s) 1. ☐ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/Paper No./Mail Date filed 1/5/04, 7/23/02 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material 	/08), 7 ⊠ Examiner's Amend 8. □ Examiner's Staten 9. □ Other	y (PTO-413), ate : diment/Comment nent of Reasons for A		
	NADIN SUPERVISOR Plaf	EG NORTON	ER	

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EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Mark Gebhardt on 2/18/04.

The application has been amended as follows:

Please replace the old abstract with this abstrate:

"An etching method for use in integrated circuit fabrication includes providing a metal nitride layer on a substrate assembly, providing regions of cobalt silicide on first portions of the metal nitride layer, and providing regions of cobalt on second portions of the metal nitride layer. The regions of cobalt and the second portions of the metal nitride layer are removed with at least one solution including a mineral acid and a peroxide. Further, the removal of the regions of cobalt and the second portions of the metal nitride layer may include a one-step process or a two-step process. In the one-step process, the regions of cobalt and the second portions of the metal nitride layer are removed with a single solution including the mineral acid and the peroxide. In the two-step process, the regions of cobalt are removed with a first solution containing a mineral acid and a peroxide and the second portions of the metal nitride layer are removed with a second solution containing a peroxide."

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2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to DuyVu n Deo whose telephone number is 571-272-1462. The examiner can normally be reached on 6:00-3:30; with alternate Friday off.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571-272-1465. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

DVD 2/18/04